One Watt Amplifier Transistor

NPN Silicon

Features

• Pb–Free Package is Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	100	Vdc
Collector-Base Voltage	V _{CBO}	100	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector Current – Continuous	Ι _C	0.5	Adc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	1.0 8.0	W m₩/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	2.5 20	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

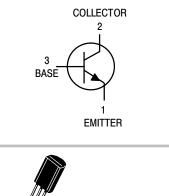
Characteristic	Symbol	Мах	Unit	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	125	°C/W	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	50	°C/W	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



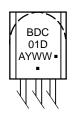
ON Semiconductor®

http://onsemi.com



TO–92 (TO–226) CASE 29–10 STYLE 1

MARKING DIAGRAM



BDC01D = Device Code

= Assembly Location

= Year

A Y

WW

- = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping
BDC01DRL1	TO-92	2000 / Tape & Reel
BDC01DRL1G	TO-92 (Pb-Free)	5000 / Tape & Reel

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	·			
Collector – Emitter Voltage ($I_C = 10 \text{ mA}, I_B = 0$)	V _{(BR)CEO}	100	_	Vdc
Collector Cutoff Current ($V_{CB} = 100 \text{ V}, I_E = 0$)	I _{CBO}	-	0.1	μAdc
Emitter Cutoff Current ($I_C = 0, V_{EB} = 5.0 V$)	I _{EBO}	-	100	nAdc
ON CHARACTERISTICS				
DC Current Gain (I _C = 100 mA, V _{CE} = 1.0 V) (I _C = 500 mA, V _{CE} = 2.0 V)	h _{FE}	40 25	400	-
Collector – Emitter Saturation Voltage (Note 1) ($I_C = 1000 \text{ mA}, I_B = 100 \text{ mA}$)	V _{CE(sat)}	-	0.7	Vdc
	V _{BE(on)}	-	1.2	Vdc
DYNAMIC CHARACTERISTICS	·			
Current Gain Bandwidth Product ($I_C = 200 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 20 \text{ MHz}$)	fT	50	_	MHz
Output Capacitance $(V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz})$	C _{ob}	-	30	pF

1. Pulse Test: Pulse Width \leq 300 µs; Duty Cycle 2.0%.

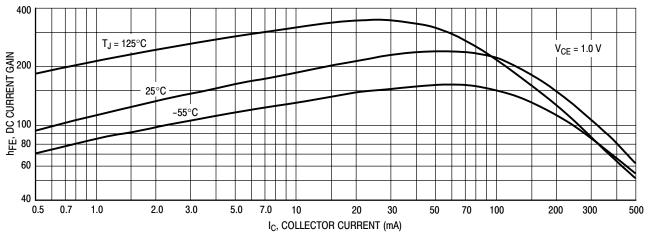
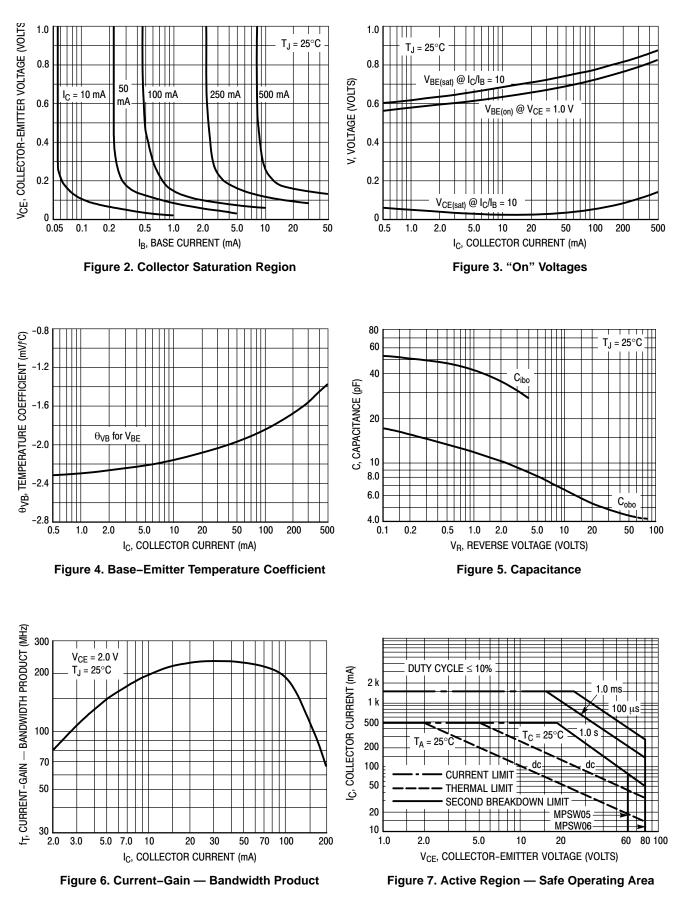
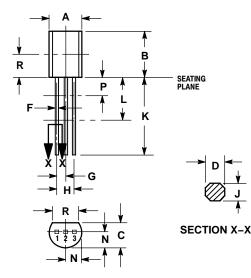


Figure 1. DC Current Gain



PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-10 ISSUE AL



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

- 2. CONTROLLING DIMENSION: INCH.
- 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- 4. DIMENSION F APPLIES BETWEEN P AND L DIMENSIONS D AND J APPLY BETWEEN L AND K MIMIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.44	5.21
В	0.290	0.310	7.37	7.87
С	0.125	0.165	3.18	4.19
D	0.018	0.021	0.457	0.533
F	0.016	0.019	0.407	0.482
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
ſ	0.018	0.024	0.46	0.61
Κ	0.500		12.70	
Г	0.250		6.35	
Ν	0.080	0.105	2.04	2.66
Ρ		0.100		2.54
R	0.135		3.43	

STYLE 14:

PIN 1. EMITTER 2. COLLECTOR

2. COLLE 3. BASE

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